

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SD1941

DESCRIPTION

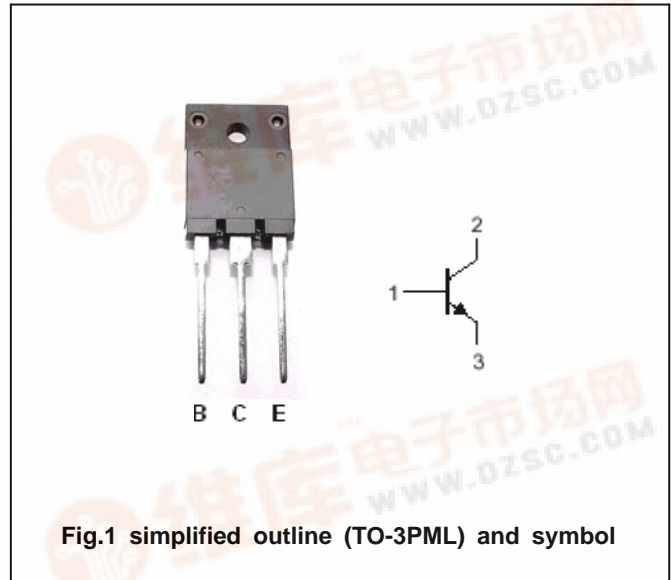
- With TO-3PML package
- High voltage ,high speed
- Low collector saturation voltage

APPLICATIONS

- Color TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings (T_a=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		6	A
I _B	Base current		3	A
P _C	Collector power dissipation	T _C =25°C	50	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A , I _B =0	600			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =1A		3.0	5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =5A ; I _B =1A			1.5	V
I _{CB0}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μ A
I _{EB0}	Emitter cut-off current	V _{EB} =5V; I _C =0			1	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	8		36	
h _{FE-2}	DC current gain	I _C =5A ; V _{CE} =5V	5			

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PACKAGE OUTLINE

